PCN Number:			20140114000				PCN Date: 01/15/2014			01/15/2014		
Title: Qualification of DFAB for (TLC5951RHAR/T) and RFAB, Carsem (Assembly) and MLA (Test) for (TPA6133A2RTJR/T)												
Customer	Contact:	PCN	Mar	ager	Phon	he: +1(214)480-6	037	C	Dept:	Qua	ality Services
*Proposed 1 st Ship Date:			4/15/2014 Estimated Sample Availability:			ble	Date Provided at Sample request					
Change T	ype:											
🛛 Assem	nbly Site			Ass	embly	Process				Assem	bly	Materials
Desigi	n			Elec	ctrical S	Specifica	ition			Mecha	nica	I Specification
🛛 Test S	Site			Pac	king/S	hipping/	Labeling			Test P	roce	SS
Wafer	Wafer Bump Site 🛛 Wafer Bump Material				Wafer Bump Process			np Process				
🛛 Wafer	Fab Site			Wafer Fab Materials					Wafer	Fab	Process	
					Part number change							
					PCI	N Deta	ils					

Description of Change:

This change notification is to announce additional Fab and Assembly/Test site options for the products shown in Groups 1 and 2 below.

Group 1 Device (TLC5951RHAR/T): Fab Only Change

Current	New
Site/Process/Wafer Diameter	Site/Process/Wafer Diameter
CFAB/LBC4 Process/200mm	DFAB/LBC4 Process/200mm

Group 2 Device (TPA6133A2RTJR/T): Fab & A/T Change

(Note: The LBC7 process was previously qualified at RFAB in 10/2010. The RTJ package was previously qualified at Carsem (CRS) in 12/2006. Details are provided in the Qual Data Section of this document.)

Current Fab	Additional Fab
Site/Process/Wafer Diameter	Site/Process/Wafer Diameter
MIHO/LBC7 Process/200mm	RFAB/LBC7 Process/300mm
Current Assembly/Test	Additional Assembly/Test
Clark-A/T	CARSEM Assembly/ MLA Test

Material Changes

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Туре	Current: Clark-A/T	New: CARSEM
Bond Wire Composition	Cu	Au

Test coverage, insertions, conditions will remain consistent with current testing and verified with test MQ.

Reason for Change:

Continuity of supply.

Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative): None

Changes to product identification resulting from this PCN:

Current

Chip Site / Assembly Site	Chip Site Code (20L)	Chip Country Code (21 L)	Assembly Site Code (22L)	Assembly Country Origin (23L)
CFAB	CU3	CHN		
міно	• MH8	JPN		
Clark-AT			QAB	PHL

Additional Sites

Chip Site /Assembly Site	Chip Site Code (20L)	Chip Country Code (21 L)	Assembly Site Code (22L)	Assembly Country Origin (23L)
DL-LIN	DLN	USA		
RFAB	RFB	USA		
CARSEM			CRS	MYS

Sample Product Shipping Label (not actual product label)



ASSEMBLY SITE CODES: TI-Clark = I, Carsem CRS = W

Product Affected:					
Group 1 Device: Additional Fab					
TLC5951RHAR	TLC5951RHAR TLC5951RHAT				
Group 2 Device: Additional Fab					
TPA6133A2RTJR	TPA6133A2RTJT				

Group 1 Device (TLC5951RHAR) Qualification Data

Qualification Data: Approved 12/18/2013

This qualification has been developed for the validation of this change. The qualification data will						
validate that the proposed change meets the applicable released technical specifications.						
Qualification Device 1: TLC5951RHA (MSL LEVEL3-260C)						
Wafer Fab Site:	DFAB	Wafer Fab Process:	LBC4			
Wafer Diameter:	200mm					

Qualification: 🗌 Plan 🛛 Test Results						
Reliability Test	Conditions	Sam Lot#1	ple Size / Lot#2	/ Fail Lot#3		
Electrical Characterization	Per datasheet specification	Pass	Pass	Pass		
**High Temp Storage Bake	170C (420 hours)	45/0	45/0	45/0		
ESD CDM	Per datasheet	3/0	3/0	3/0		
ESD HBM	Per datasheet	3/0	3/0	3/0		
Latch-up	Per JESD78	6/0	6/0	6/0		
Early Life Failure Rate	125C (24 hours)	1000/0	1000/0	1000/0		
High Temp Operating Life	140C (480 hours)	80/0	80/0	80/0		
**Temp Cycle	-65/150C (500 cycles)	77/0	77/0	77/0		
**Biased HAST	130C/85%RH (96 hours)	80/0	80/0	80/0		
**Preconditioning: Level 3-260C			•			

Group 2 Device (TPA6133A2RTJR/T) Reference Qual Data Qualification of LBC7 process at RFAB

Qualification Data: Approved: 10/06/2010

This qualification has been developed for the validation of this change. The qualification data will validate that the proposed change meets the applicable released technical specifications.

Qualification Device: TPS51217DSC							
Wafer Fab Site:	RFAB	Metallization:	TiN/AlCu.5/TiN	١			
Wafer Fab Process:	LBC7	Wafer diameter:	300mm				
Qualification:	Plan 🛛 🛛 Test	Results					
Reliability Test		Conditions		Sam	ple Size	/Fail	
		Conditions		Lot#1	Lot#2	Lot#3	
Electrical Characteriza	ition	Per datasheet spec		Pass	Pass	Pass	
Latch-up		(per JESD78)		6/0	6/0	6/0	
**Biased HAST		130C/85%RH (96 Hrs)		77/0	77/0	77/0	
ESD HBM		1000V		3/0	3/0	3/0	
ESD CDM		250V		3/0	3/0	3/0	
High Temp. Storage B	ake	170C (420 Hrs)		77/0	77/0	77/0	
**Autoclave 121C		121C, (96 Hrs)		77/0	77/0	77/0	
**T/C -65C/150C		-65C/+150C (500Cycles)		77/0	77/0	77/0	
Steady-state Life Test	(See Note 1)	135C (635 Hrs)		77/0	77/0	77/0	
**Preconditioning: MS	SL 2@260C						

Note 1: Life test equivalent conditions

125C, 1000hrs 135C, 635hrs 140C, 480hrs

150C, 300hrs

Qualification of RTJ Package at Carsem (CRS)

Qualification Data: Approved 12/02/2006

This qualification has been specifically developed for the validation of this change. The qualification data validates that the proposed change meets the applicable released technical specifications.

Qual Vehicle: TPA6130A2RTJ (MSL 2-260C)							
Package Construction Details							
Assembly Site:	CRS	Mold Compound:	435370				
# Pins-Designator, Family:	20-RTJ, QFN	Mount Compound:	439525				
Leadframe (Finish, Base):	NiPdAu	Bond Wire:	1.0 Mil Dia., Au				
Qualification: 🗌 Plan	🛛 Test Results	.					
Reliability Test		Conditions	Sample Size Pass / Fail Lot 1				
**Life Test, 140C		480 Hours	116/0				
**Thermal Shock, -65/150C		500 Cycles	77/0				
ESD HBM		1000V	3/0				
ESD CDM		250V	3/0				
Electrical Characterization		-	Pass				
Latch-up		Per JESD78	6/0				
**- Preconditioning sequence: Level 2-260C.							

Additional Reference: Qualification of QFN Package

Qualification Data: Approved 06/11/2004

This qualification has been specifically developed for the validation of this change. The qualification data validates that the proposed change meets the applicable released technical specifications.

Qual Vehicle 1: TPS65010RGZ (MSL 2-260C)

Package Construction Details							
Assembly Site: CRS Mold Compound: 435370							
# Pins-Designator, Family:	48-RGZ, QFN	Mount Compound:	435143				
Leadframe (Finish, Base):	NiPdAu	Bond Wire:	1.3 Mil Dia., Au				
Qualification: Plan X Test Results							

	Conditions	Sample Size			
Reliability Test			Pass / Fail		
		Lot 1	Lot 2	Lot3	
**Life Test, 150C	300 Hours	40/0	40/0	40/0	
**HAST 130C/85%RH	96 Hours	77/0	77/0	77/0	
**Autoclave, 121C	96 Hours	77/0	77/0	77/0	
**Thermal Shock, -65/150C	500 Cycles	77/0	77/0	77/0	
**Temp Cycle, -65/+150C	500 Cycles	77/0	77/0	77/0	
**High-Temp Storage, 170C	420 hours	30/0	30/0	30/0	
Solvent Resistance		12/0	12/0	12/0	
**- Preconditioning sequence: Level 2-260C.					

Qual Vehicle 2: TPA2005D1 (MSL 2-260C)								
Package Construction Details								
Assembly Sit	e: CRS	Mold Compour	nd: 435	435370				
# Pins-Designator, Famil	y: 8-DRB, QFN	Mount Compour	nd: 435	435143				
Leadframe (Finish, Base	inish, Base): NiPdAu B		re: 1.0 Mil Dia., Au					
Qualification: 🗌 Plan 🛛 Test Results								
Reliability Test	Conditions	onditions		Sample Size Pass / Fail				
,			Lot 1	Lot 2	Lot 3			
**Life Test, 155C	240 Hours		116/0	-	-			
**HAST 130C/85%RH	96 Hours		77/0	77/0	77/0			
**Autoclave, 121C	96 Hours		77/0	77/0	77/0			
**Thermal Shock, -65/150C	500 Cycles		77/0	77/0	77/0			
Temp Cycle, -65/+150C	500 Cycles		77/0	77/0	77/0			
**High-Temp Storage, 170C	420 hours		77/0	-	-			
**- Preconditioning sequence: Level 2-260C.								

For questions regarding this notice, e-mails can be sent to the regional contacts shown below or your local Field Sales Representative.

Location	E-Mail
USA	PCNAmericasContact@list.ti.com
Europe	PCNEuropeContact@list.ti.com
Asia Pacific	PCNAsiaContact@list.ti.com
Japan	PCNJapanContact@list.ti.com